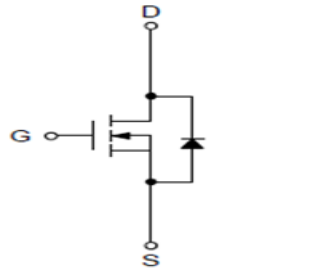
POWER MOSFET

Features

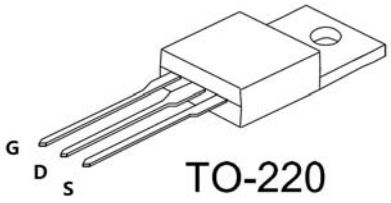
- 150V,80A N-Channel MOSFET
- $R_{DS(on)(typ.)}$=17mΩ @V_{GS}=10V
- High ruggedness
- Fast switching
- 100% avalanche tested
- Exceptional dv/dt capability



N-Channel MOSFET

Applications

- Switching application
- Motor drive



TO-220

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	±25	V
I_D	Continuous Drain Current(TC=25℃)	80	A
	Continuous Drain Current(TC=100℃)	70	A
I_{DM}	Pulsed Drain Current(Note 1)	300	A
EAS	Single Pulsed Avalanche Energy(Note 2)	400	mJ
P_D	Maximum Power Dissipation (T_C=25 ℃)	176	W
	Maximum Power Dissipation (T_C=100℃)	90	W
T_J	Maximum Junction Temperature	175	℃
T_{STG}	Storage Temperature Range	-55 to +175	℃

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

2.Starting T_J=25℃,L=1.0mH,R_G=25Ω,I_D=37A,V_{GS}=10V

Thermal data

Symbol	Parameter	Max.	Units
$R_{th\ J\text{-}C}$	Thermal Resistance, Junction to case	0.45	℃/ W

Electrical Characteristics (TC=25℃ unless otherwise noted)

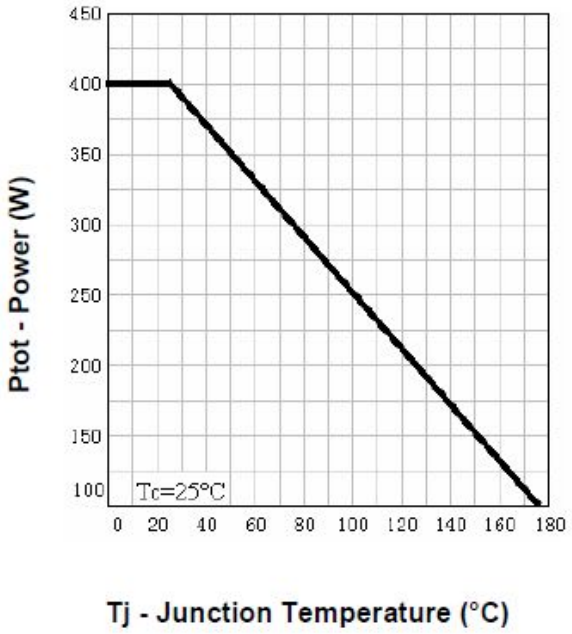
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	150			V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=100V, V_{GS}=0V			1	uA
I_{GSS}	Gate Leakage Current, Forward	V_{GS}=25V, V_{DS}=0V			100	nA
	Gate Leakage Current, Reverse	V_{GS}= -25V, V_{DS}=0V			-100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS}, I_D=250uA	2	3	4	V
$R_{DS(on)}$	Collector-Emitter Saturation Voltage	V_{GS}=10V, I_D=40A		17	20	mΩ
gfs	Forward Transconductance	V_{DS}=15V, I_D=40A		25		S
Q_g	Total Gate Charge	V_{DS}=30V V_{GS}=10V I_D=40A		170	240	nC
Q_{gs}	Gate-Source Charge			55		nC
Q_{gd}	Gate-Drain Charge			60		nC
$t_{d(on)}$	Turn-on Delay Time	VDD=35V,RL=35Ω VGEN=10V ID=1A RG=6Ω	-	26	-	ns
t_r	Turn-on Rise Time		-	46	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	129	-	ns
t_f	Turn-off Fall Time		-	88	-	ns
C_{iss}	Input Capacitance	V_{DS}=30V V_{GS}=0V f = 1MHz	-	6900	-	pF
C_{oss}	Output Capacitance		-	1100	-	pF
C_{rss}	Reverse Transfer Capacitance		-	519	-	pF
R_{Gint}	Integrated gate resistor			1.05		Ω

Source-Drain Ratings and Characteristics (T_C=25℃ unless otherwise noted)

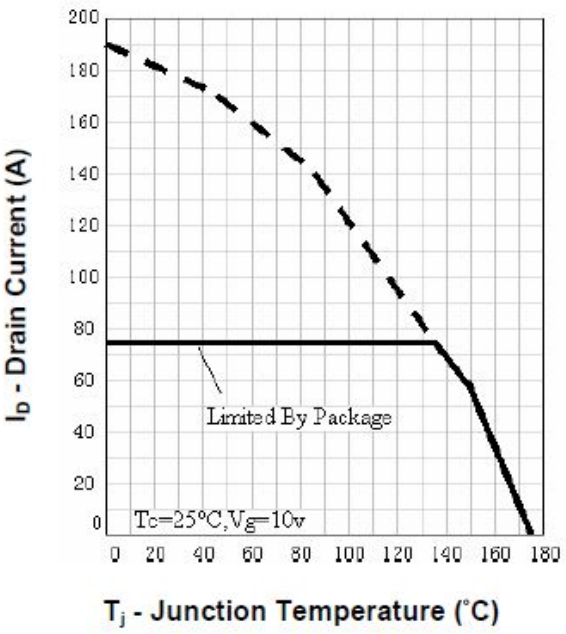
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage	V_{GS}=0V,I_{SD}=60A	-	0.8	1.3	V
I_S	Continuous Diode Forward Current				130	A
t_{rr}	Reverse Recovery Time	I_{SD}=60A dI_F/dt=100A/us	-	68		ns
Q_{rr}	Reverse Recovery Charge		-	130		nC

Typical Characteristics

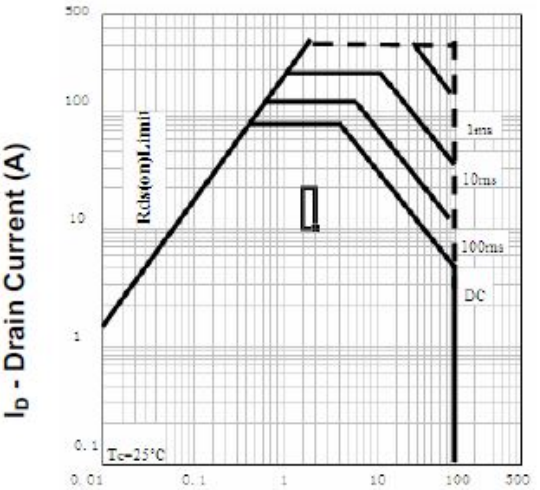
Power Dissipation



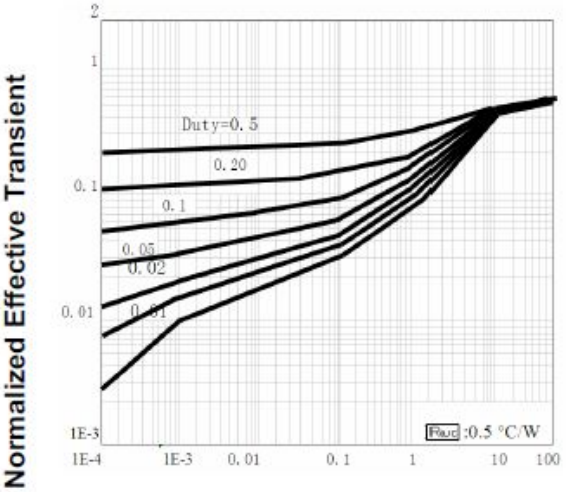
Drain Current



Safe Operation Area

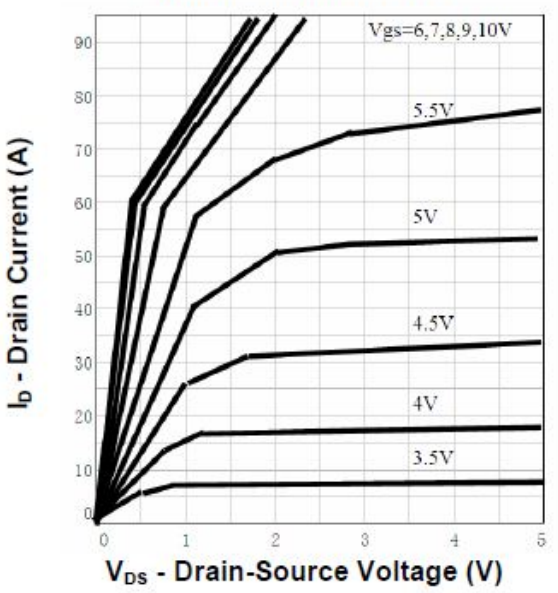


Thermal Transient Impedance

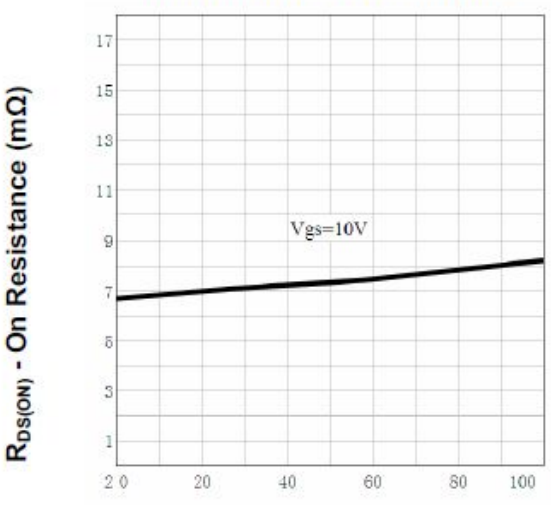


Typical Characteristics

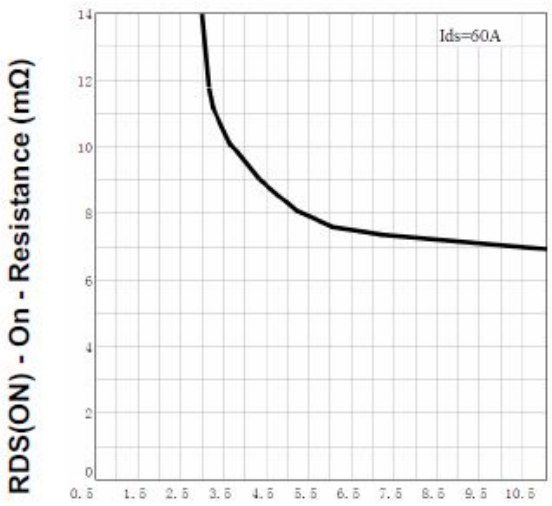
Output Characteristics



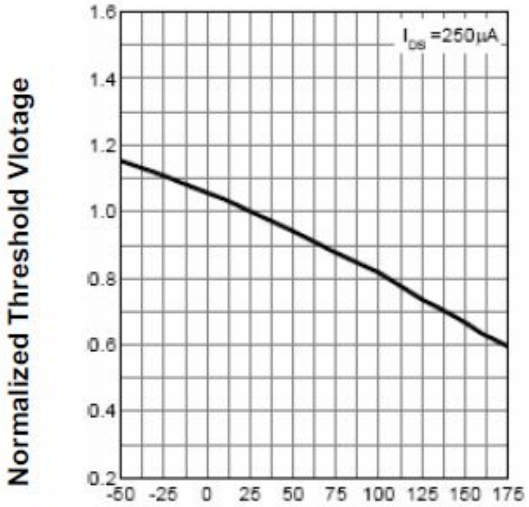
Drain-Source On Resistance



Drain-Source On Resistance

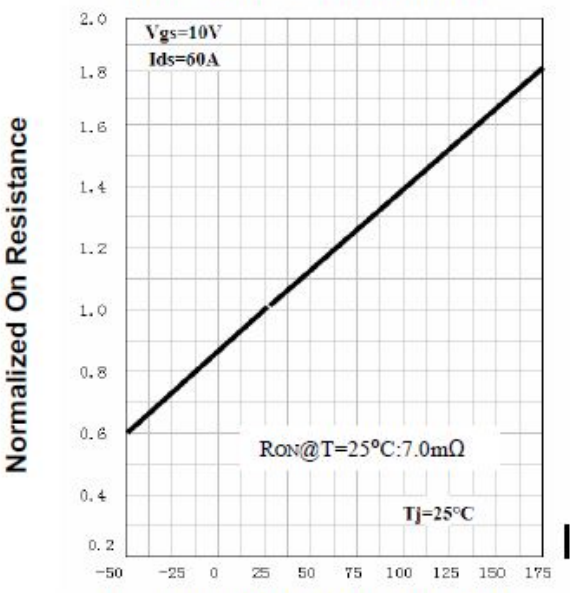


Gate Threshold Voltage

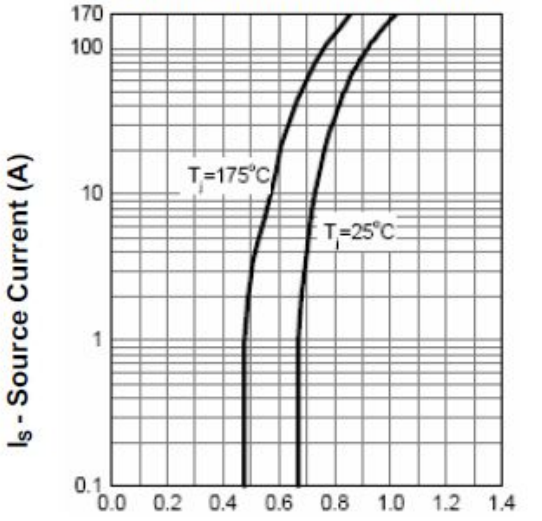


Typical Characteristics

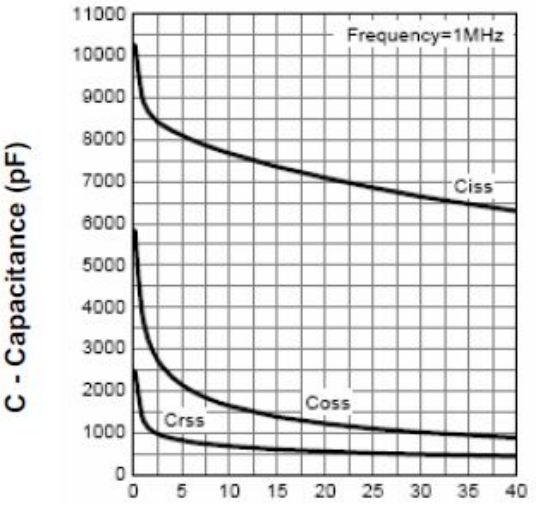
Drain-Source On Resistance



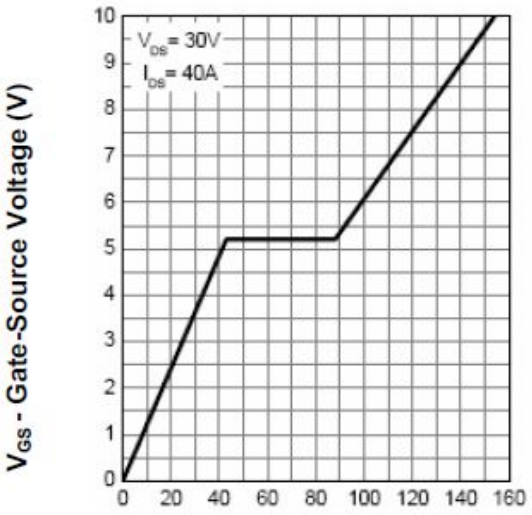
Source-Drain Diode Forward



Capacitance

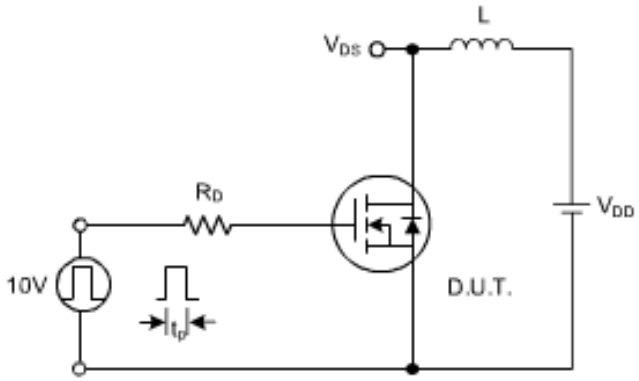


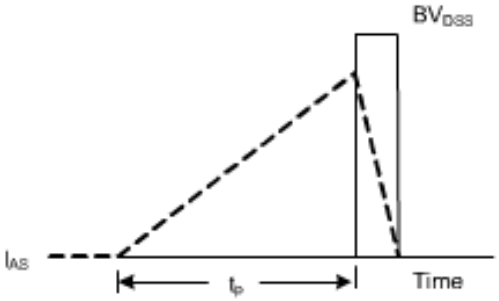
Gate Charge



Test Circuits

Avalanche test circuits and waveforms





Gate charge test circuits and waveforms